A4 cont'd

26. A light emitting device according to claim 21, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

A5

39. A light emitting device according to claim 37, wherein the first, second, and third switching elements are p-channel thin film transistors.

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45. A light emitting device according to claim 37, wherein the conductor is made of the same material as a gate electrode of the first, second, and third switching element.

46. A light emitting device according to claim 37, wherein at least one of the first, second, and third switching element comprises at least one thin film transistor.

A7

50. A light emitting device according to claim 49, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having a concentration gradient at least at an impurity concentration of $1 \times 10^{17}$ to $1 \times 10^{18}$ / $cm^3$, and the impurity concentration is increased as a distance from the channel forming region increases.

A8

55. A light emitting device according to claim 52, wherein the first, second, and third switching elements are p-channel thin film transistors.

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61. A light emitting device according to claim 52, wherein the conductor is made of the same material as a gate electrode of the switching element.

A10

65. A light emitting device according to claim 64, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having a concentration gradient at least at an impurity concentration of $1 \times 10^{17}$ to $1 \times 10^{18}$ / $cm^3$, and the impurity concentration is increased as a distance from the channel forming region increases.

69. A method of manufacturing a light emitting device according to claim 67, wherein forming the conductive coating further comprises connecting the conductor with a wiring to be the same potential.

70. A method of manufacturing a light emitting device according to claim 69, further comprising separating the wiring using a laser light after forming the conductive coating.

71. A method of manufacturing a light emitting device according to claim 69, further comprising separating the wiring simultaneously with the substrate after plating.

74. A method of manufacturing a light emitting device according to claim 72, wherein forming the conductive coating further comprises connecting the conductor with a wiring to be the same potential.

75. A method of manufacturing a light emitting device according to claim 74, further comprising separating the wiring using a laser light after forming the conductive coating.

76. A method of manufacturing a light emitting device according to claim 74, further comprising separating the wiring simultaneously with the substrate after plating.